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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	36MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	80
Program Memory Size	768KB (768K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f101vft6tr

2.3.19 I²C bus

Up to two I²C bus interfaces can operate in multi-master and slave modes. They support standard and fast modes.
They support 7/10-bit addressing mode and 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded.
They can be served by DMA and they support SMBus 2.0/PMBus.

2.3.20 Universal synchronous/asynchronous receiver transmitters (USARTs)

The STM32F101xF and STM32F101xG access line embeds three universal synchronous/asynchronous receiver transmitters (USART1, USART2 and USART3) and two universal asynchronous receiver transmitters (UART4 and UART5).

These five interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability. The five interfaces are able to communicate at speeds of up to 2.25 Mbit/s.

USART1, USART2 and USART3 also provide hardware management of the CTS and RTS signals, Smart Card mode (ISO 7816 compliant) and SPI-like communication capability. All interfaces can be served by the DMA controller except for UART5.

2.3.21 Serial peripheral interface (SPI)

Up to three SPIs are able to communicate up to 18 Mbits/s in slave and master modes in full-duplex and simplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

All SPIs can be served by the DMA controller.

2.3.22 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high current-capable.

The I/Os alternate function configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.

2.3.23 ADC (analog to digital converter)

A 12-bit analog-to-digital converter is embedded into STM32F101xF and STM32F101xG access line devices. It has up to 16 external channels, performing conversions in single-shot or scan modes. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADC can be served by the DMA controller.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

5 Electrical characteristics

5.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

5.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3Σ).

5.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.3 V (for the 2 V ≤ V_{DD} ≤ 3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2Σ).

5.1.3 Typical curves

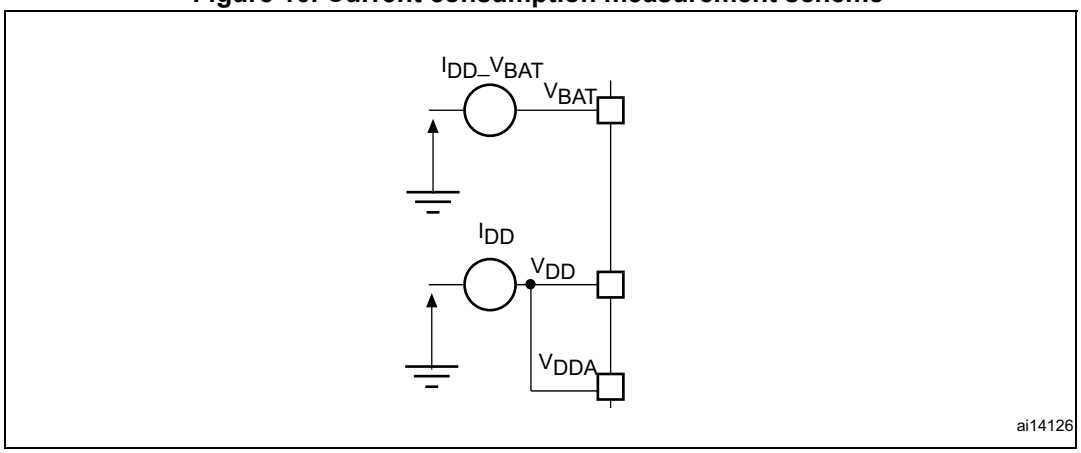
Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

5.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 7*.

5.1.7 Current consumption measurement

Figure 10. Current consumption measurement scheme



5.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 7: Voltage characteristics*, *Table 8: Current characteristics*, and *Table 9: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 7. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
V_{DD} –V_{SS}	External main supply voltage (including V_{DDA} and V_{DD})(1)	–0.3	4.0	V
V_{IN}(2)	Input voltage on five volt tolerant pin	V_{SS} –0.3	V_{DD} +4.0	
	Input voltage on any other pin	V_{SS} –0.3	4.0	
$\|\Delta V_{DDx}\|$	Variations between different V_{DD} power pins	-	50	mV
$\|V_{SSX} - V_{SS}\|$	Variations between all the different ground pins including V_{REF-}	-	50	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see *Section 5.3.12: Absolute maximum ratings (electrical sensitivity)*		-

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to *Table 8: Current characteristics* for the maximum allowed injected current values.

5.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 12* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 10*.

Table 12. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.1	2.18	2.26	V
		PLS[2:0]=000 (falling edge)	2	2.08	2.16	V
		PLS[2:0]=001 (rising edge)	2.19	2.28	2.37	V
		PLS[2:0]=001 (falling edge)	2.09	2.18	2.27	V
		PLS[2:0]=010 (rising edge)	2.28	2.38	2.48	V
		PLS[2:0]=010 (falling edge)	2.18	2.28	2.38	V
		PLS[2:0]=011 (rising edge)	2.38	2.48	2.58	V
		PLS[2:0]=011 (falling edge)	2.28	2.38	2.48	V
		PLS[2:0]=100 (rising edge)	2.47	2.58	2.69	V
		PLS[2:0]=100 (falling edge)	2.37	2.48	2.59	V
		PLS[2:0]=101 (rising edge)	2.57	2.68	2.79	V
		PLS[2:0]=101 (falling edge)	2.47	2.58	2.69	V
		PLS[2:0]=110 (rising edge)	2.66	2.78	2.9	V
		PLS[2:0]=110 (falling edge)	2.56	2.68	2.8	V
		PLS[2:0]=111 (rising edge)	2.76	2.88	3	V
		PLS[2:0]=111 (falling edge)	2.66	2.78	2.9	V
$V_{PVDhyst}$(2)	PVD hysteresis	-	-	100	-	mV
$V_{POR/PDR}$	Power on/power down reset threshold	Falling edge	1.8(1)	1.88	1.96	V
		Rising edge	1.84	1.92	2.0	V
$V_{PDRhyst}$(2)	PDR hysteresis	-	-	40	-	mV
$t_{RSTTEMPO}$(2)	Reset temporization	-	1.5	2.5	3.5	ms

1. The product behavior is guaranteed by design down to the minimum $V_{POR/PDR}$ value.
2. Guaranteed by design.

Table 21. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency(1)	-	1	8	25	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	OSC_IN high or low time(1)		5	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time(1)		-	-	20	
$C_{in(HSE)}$	OSC_IN input capacitance(1)	-	-	5	-	pF
$DuCy_{(HSE)}$	Duty cycle	-	45	-	55	%
I_L	OSC_IN Input leakage current	$V_{SS} \le V_{IN} \le V_{DD}$	-	-	±1	µA

1. Guaranteed by design.

Low-speed external user clock generated from an external source

The characteristics given in *Table 22* result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 10*.

Table 22. Low-speed user external clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User external clock source frequency(1)	-	-	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage	-	$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage	-	V_{SS}	-	$0.3V_{DD}$	
$t_{w(LSE)}$ $t_{w(LSE)}$	OSC32_IN high or low time(1)	-	450	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time(1)	-	-	-	50	
$C_{in(LSE)}$	OSC32_IN input capacitance(1)	-	-	5	-	pF
$DuCy_{(LSE)}$	Duty cycle	-	30	-	70	%
I_L	OSC32_IN Input leakage current	$V_{SS} \le V_{IN} \le V_{DD}$	-	-	±1	µA

1. Guaranteed by design.

Figure 15. High-speed external clock source AC timing diagram

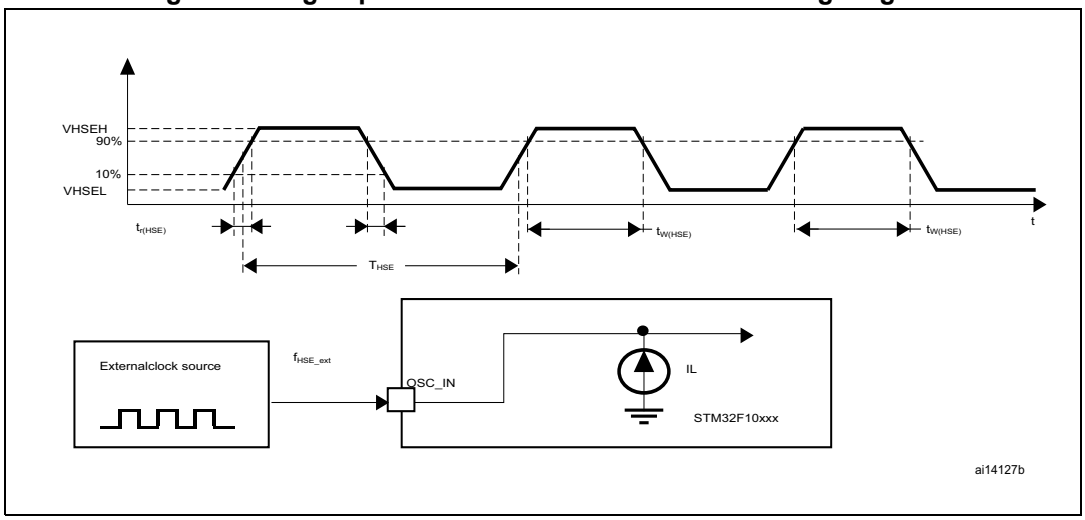
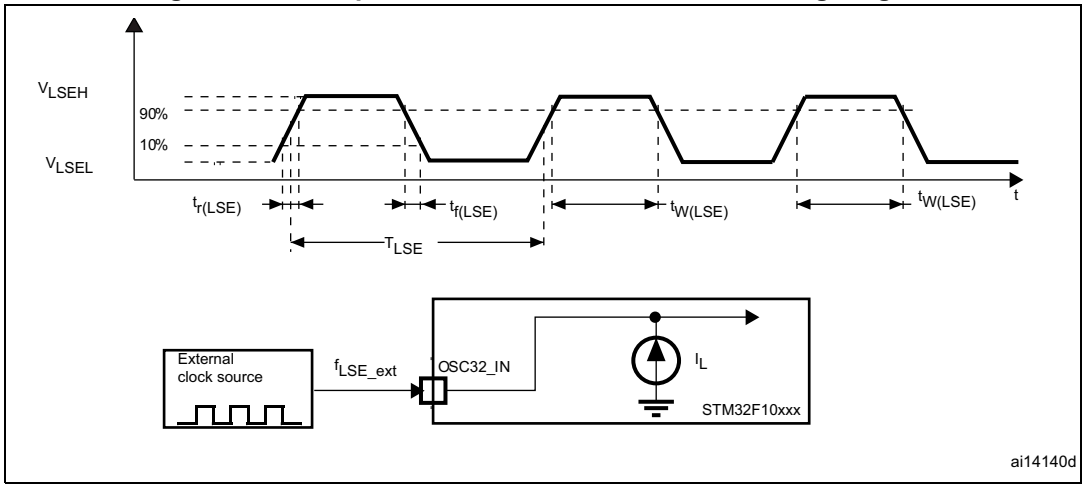


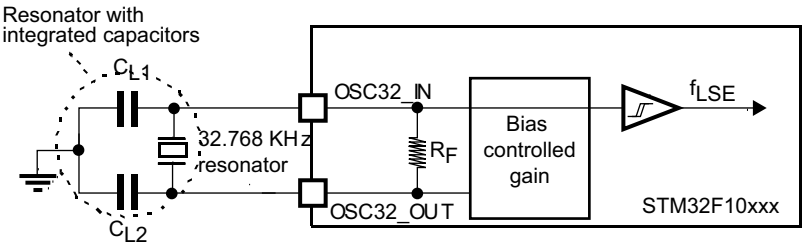
Figure 16. Low-speed external clock source AC timing diagram



Note: For C_{L1} and C_{L2}, it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}.
Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

Caution: To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF) it is strongly recommended to use a resonator with a load capacitance $C_L \leq 7$ pF. Never use a resonator with a load capacitance of 12.5 pF.
Example: if you choose a resonator with a load capacitance of C_L = 6 pF, and C_{stray} = 2 pF, then $C_{L1} = C_{L2}$ = 8 pF.

Figure 18. Typical application with a 32.768 kHz crystal



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5.3.7 Internal clock source characteristics

The parameters given in *Table 25* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 10*.

High-speed internal (HSI) RC oscillator

Table 25. HSI oscillator characteristics(1)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
f_{HSI}	Frequency	-		-	8	-	MHz
$DuCy_{(HSI)}$	Duty cycle	-		45	-	55	%
ACC_{HSI}	Accuracy of the HSI oscillator	User-trimmed with the RCC_CR register(2)		-	-	1(3)	%
		Factory-calibrated(4)	T_A = –40 to 105 °C	–2	-	2.5	%
			T_A = –10 to 85 °C	–1.5	-	2.2	%
			T_A = 0 to 70 °C	–1.3	-	2	%
			T_A = 25 °C	–1.1	-	1.8	%
$t_{su(HSI)}$(4)	HSI oscillator startup time	-		1	-	2	µs
$I_{DD(HSI)}$(4)	HSI oscillator power consumption	-		-	80	100	µA

1. V_{DD} = 3.3 V, T_A = –40 to 85 °C unless otherwise specified.

2. Refer to application note AN2868 “STM32F10xxx internal RC oscillator (HSI) calibration” available from the ST website *www.st.com*
3. Guaranteed by design.
4. Guaranteed by characterization results.

Low-speed internal (LSI) RC oscillator

Table 26. LSI oscillator characteristics (1)

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}(2)	Frequency	30	40	60	kHz
$t_{su(LSI)}$(3)	LSI oscillator startup time	-	-	85	µs
$I_{DD(LSI)}$(3)	LSI oscillator power consumption	-	0.65	1.2	µA

1. V_{DD} = 3 V, T_A = –40 to 85 °C unless otherwise specified.
2. Guaranteed by characterization results.
3. Guaranteed by design.

Wakeup time from low-power mode

The wakeup times given in *Table 27* are measured on a wakeup phase with an 8-MHz HSI RC oscillator. The clock source used to wake up the device depends from the current operating mode:

- Stop or Standby mode: the clock source is the RC oscillator
- Sleep mode: the clock source is the clock that was set before entering Sleep mode.

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 10*.

Table 27. Low-power mode wakeup timings

Symbol	Parameter	Typ	Unit
$t_{WUSLEEP}$(1)	Wakeup from Sleep mode	1.8	µs
t_{WUSTOP}(1)	Wakeup from Stop mode (regulator in run mode)	3.6	µs
	Wakeup from Stop mode (regulator in low-power mode)	5.4	
$t_{WUSTDBY}$(1)	Wakeup from Standby mode	50	µs

1. The wakeup times are measured from the wakeup event to the point at which the user application code reads the first instruction.

Table 30. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min(1)	
N_{END}	Endurance	T_A = –40 °C to 85 °C	10	kcycles
t_{RET}	Data retention	T_A = 85 °C, 1 kcycle(2)	30	Years
		T_A = 55 °C, 10 kcycle(2)	20	

1. Guaranteed by characterization results.
2. Cycling performed over the whole temperature range.

5.3.10 FSMC characteristics

Asynchronous waveforms and timings

Figure 19 through *Figure 22* represent asynchronous waveforms and *Table 31* through *Table 34* provide the corresponding timings. The results shown in these tables are obtained with the following FSMC configuration:

- AddressSetupTime = 0
- AddressHoldTime = 1
- DataSetupTime = 1

Figure 24. Synchronous multiplexed PSRAM write timings

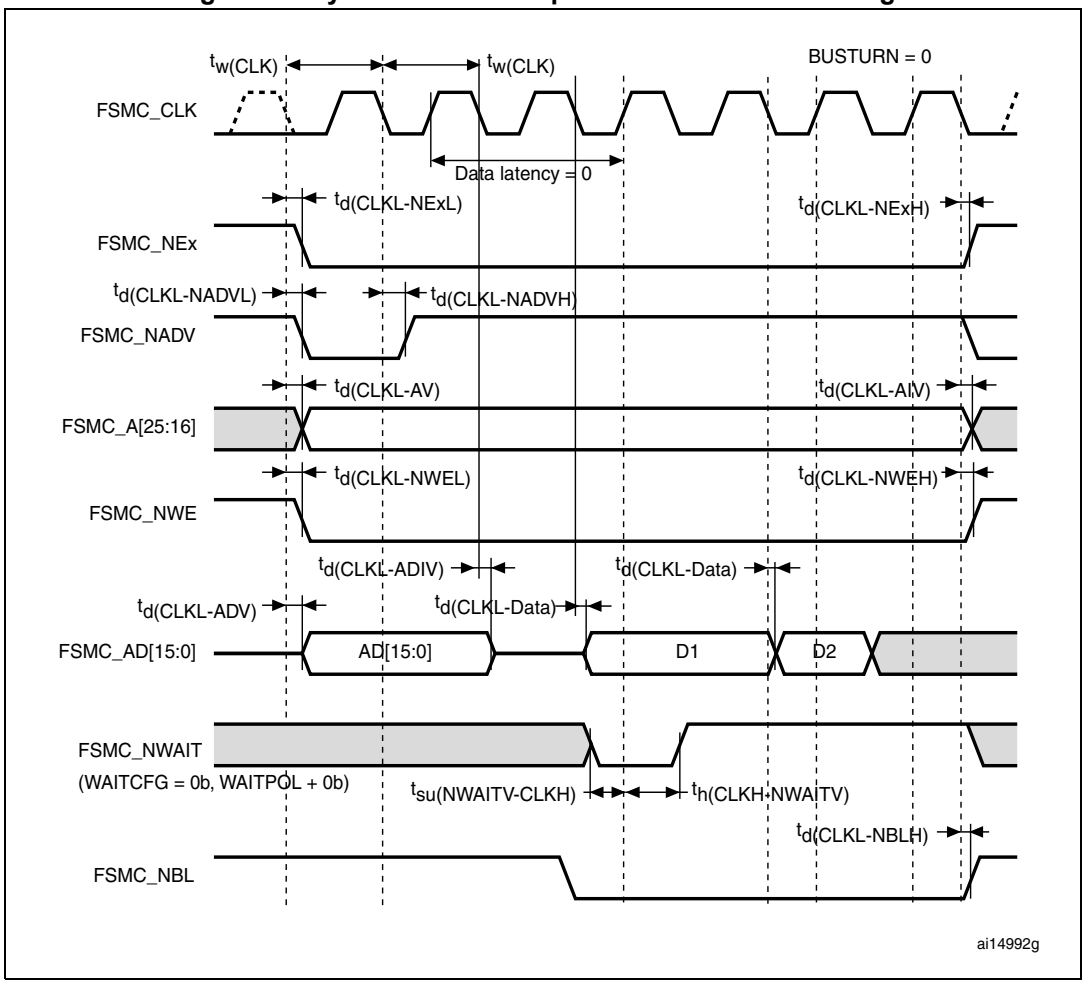


Figure 25. Synchronous non-multiplexed NOR/PSRAM read timings

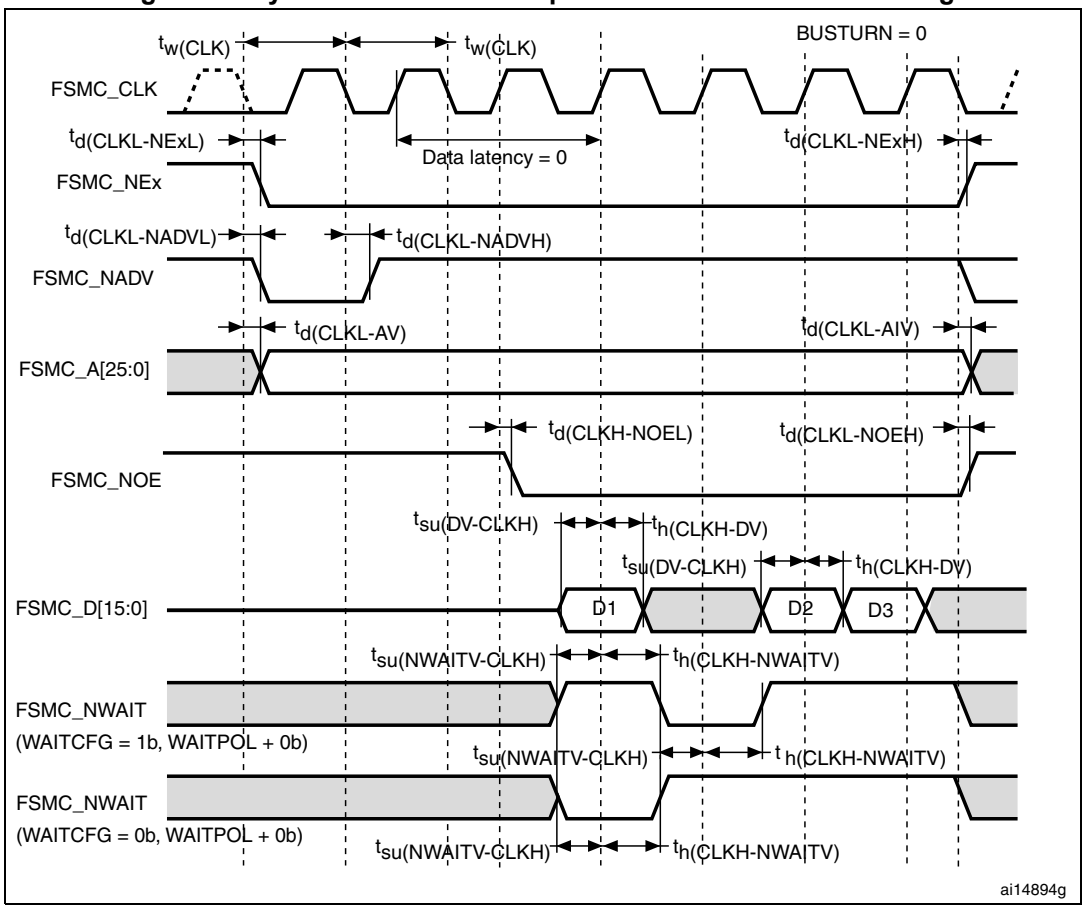


Table 37. Synchronous non-multiplexed NOR/PSRAM read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	27.6	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x = 0...2)	-	1.5	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x = 0...2)	2	-	ns
$t_{d(CLKL-NADVL)}$	FSMC_CLK low to FSMC_NADV low	-	0.5	ns
$t_{d(CLKL-NADVH)}$	FSMC_CLK low to FSMC_NADV high	1	-	ns
$t_{d(CLKL-AV)}$	FSMC_CLK low to FSMC_Ax valid (x = 0...25)	-	0	ns
$t_{d(CLKL-AIV)}$	FSMC_CLK low to FSMC_Ax invalid (x = 0...25)	2	-	ns
$t_{d(CLKL-NOEL)}$	FSMC_CLK low to FSMC_NOE low	-	t_{HCLK} + 1	ns
$t_{d(CLKL-NOEH)}$	FSMC_CLK low to FSMC_NOE high	1.5	-	ns
$t_{su(DV-CLKH)}$	FSMC_D[15:0] valid data before FSMC_CLK high	3.5	-	ns
$t_{h(CLKH-DV)}$	FSMC_D[15:0] valid data after FSMC_CLK high	0	-	ns
$t_{su(NWAITV-CLKH)}$	FSMC_NWAIT valid before FSMC_SMCLK high	7	-	ns
$t_{h(CLKH-NWAITV)}$	FSMC_NWAIT valid after FSMC_CLK high	2	-	ns

1. C_L = 15 pF.

Table 40. Switching characteristics for PC Card/CF read and write cycles in I/O space

Symbol	Parameter	Min	Max	Unit
$tw_{(NIOWR)}$	FSMC_NIOWR low width	8 THCLK	-	ns
$tv_{(NIOWR-D)}$	FSMC_NIOWR low to FSMC_D[15:0] valid	-	5 THCLK - 4	ns
$th_{(NIOWR-D)}$	FSMC_NIOWR high to FSMC_D[15:0] invalid	11THCLK - 7	-	ns
$td_{(NCE4\_1-NIOWR)}$	FSMC_NCE4_1 low to FSMC_NIOWR valid	-	5THCLK + 1	ns
$th_{(NCEx-NIOWR)}$	FSMC_NCEx high to FSMC_NIOWR invalid	5THCLK - 2.5	-	ns
$td_{(NIORD-NCEx)}$	FSMC_NCEx low to FSMC_NIORD valid	-	5THCLK - 0.5	ns
$th_{(NCEx-NIORD)}$	FSMC_NCEx high to FSMC_NIORD) valid	5 THCLK - 0.5	-	ns
$tw_{(NIORD)}$	FSMC_NIORD low width	8THCLK	-	ns
$tsu_{(D-NIORD)}$	FSMC_D[15:0] valid before FSMC_NIORD high	28	-	ns
$td_{(NIORD-D)}$	FSMC_D[15:0] valid after FSMC_NIORD high	3	-	ns

NAND controller waveforms and timings

Figure 33 through *Figure 36* represent synchronous waveforms and *Table 40* and *Table 41* provide the corresponding timings. The results shown in this table are obtained with the following FSMC configuration:

- COM.FSMC_SetupTime = 0x00;
- COM.FSMC_WaitSetupTime = 0x02;
- COM.FSMC_HoldSetupTime = 0x02;
- COM.FSMC_HiZSetupTime = 0x00;
- ATT.FSMC_SetupTime = 0x01;
- ATT.FSMC_WaitSetupTime = 0x02;
- ATT.FSMC_HoldSetupTime = 0x01;
- ATT.FSMC_HiZSetupTime = 0x00;
- Bank = FSMC_Bank_NAND;
- MemoryDataWidth = FSMC_MemoryDataWidth_16b;
- ECC = FSMC_ECC_Enable;
- ECCPageSize = FSMC_ECCPageSize_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0;

The test results are given in *Table 46*

Table 46. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on OSC_IN32, OSC_OUT32, PA4, PA5, PC13	-0	+0	mA
	Injected current on all FT pins	-5	+0	
	Injected current on any other pin	-5	+5	

Output voltage levels

Unless otherwise specified, the parameters given in *Table 48* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 10*. All I/Os are CMOS and TTL compliant.

Table 48. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}(1)	Output Low level voltage for an I/O pin when 8 pins are sunk at the same time	CMOS port(2), I_{IO} = +8 mA, 2.7 V < V_{DD} < 3.6 V	-	0.4	V
V_{OH}(3)	Output High level voltage for an I/O pin when 8 pins are sourced at the same time		V_{DD}–0.4	-	
V_{OL}(1)	Output low level voltage for an I/O pin when 8 pins are sunk at the same time	TTL port(2) I_{IO} = +8 mA 2.7 V < V_{DD} < 3.6 V	-	0.4	V
V_{OH}(3)	Output high level voltage for an I/O pin when 8 pins are sourced at the same time		2.4	-	
V_{OL}(1)	Output low level voltage for an I/O pin when 8 pins are sunk at the same time	I_{IO} = +20 mA(4) 2.7 V < V_{DD} < 3.6 V	-	1.3	V
V_{OH} (3)	Output high level voltage for an I/O pin when 8 pins are sourced at the same time		V_{DD}–1.3	-	
V_{OL}(1)	Output low level voltage for an I/O pin when 8 pins are sunk at the same time	I_{IO} = +6 mA(4) 2 V < V_{DD} < 2.7 V	-	0.4	V
V_{OH}(3)	Output high level voltage for an I/O pin when 8 pins are sourced at the same time		V_{DD}–0.4	-	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 8* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 8* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD}.
4. Guaranteed by characterization results.

Table 56. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Power supply	-	2.4	-	3.6	V
V_{REF+}	Positive reference voltage	-	2.4	-	V_{DDA}	V
V_{REF-}	Negative reference voltage	-	-	0	-	V
I_{VREF}	Current on the V_{REF} input pin	-	-	160	220(1)	µA
f_{ADC}	ADC clock frequency	-	0.6	-	14	MHz
f_S(2)	Sampling rate	-	0.05	-	1	MHz
f_{TRIG}(2)	External trigger frequency	f_{ADC} = 14 MHz	-	-	823	kHz
		-	-	-	17	$1/f_{ADC}$
V_{AIN}	Conversion voltage range(3)	-	0 (V_{SSA} or V_{REF-} tied to ground)	-	V_{REF+}	V
R_{AIN}(2)	External input impedance	See *Equation 1* and *Table 57* for details	-	-	50	kΩ
R_{ADC}(2)	Sampling switch resistance	-	-	-	1	kΩ
C_{ADC}(2)	Internal sample and hold capacitor	-	-	-	8	pF
t_{CAL}(2)	Calibration time	f_{ADC} = 14 MHz	5.9			µs
		-	83			$1/f_{ADC}$
t_{lat}(2)	Injection trigger conversion latency	f_{ADC} = 14 MHz	-	-	0.214	µs
		-	-	-	3(4)	$1/f_{ADC}$
t_{latr}(2)	Regular trigger conversion latency	f_{ADC} = 14 MHz	-	-	0.143	µs
		-	-	-	2(4)	$1/f_{ADC}$
t_S(2)	Sampling time	f_{ADC} = 14 MHz	0.107	-	17.1	µs
		-	1.5	-	239.5	$1/f_{ADC}$
t_{STAB}(2)	Power-up time	-	0	0	1	µs
t_{CONV}(2)	Total conversion time (including sampling time)	f_{ADC} = 14 MHz	1	-	18	µs
		-	14 to 252 (t_S for sampling +12.5 for successive approximation)			$1/f_{ADC}$

1. Guaranteed by characterization results.
2. Guaranteed by design.
3. V_{REF+} can be internally connected to V_{DDA} and V_{REF-} can be internally connected to V_{SSA}, depending on the package. Refer to *Section 3: Pinouts and pin descriptions* for further details.
4. For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in *Table 56*.

Equation 1: R_{AIN} max formula:

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 57. R_{AIN} max for f_{ADC} = 14 MHz(1)

T_s (cycles)	t_S (µs)	R_{AIN} max (kΩ)
1.5	0.11	0.4
7.5	0.54	5.9
13.5	0.96	11.4
28.5	2.04	25.2
41.5	2.96	37.2
55.5	3.96	50
71.5	5.11	NA
239.5	17.1	NA

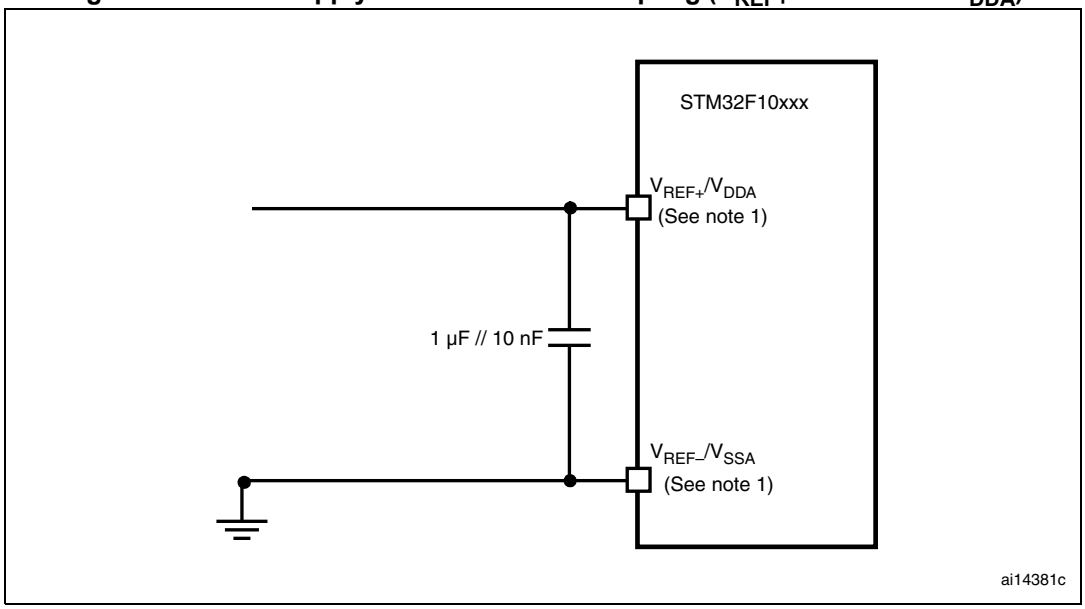
1. Guaranteed by design.

Table 58. ADC accuracy - limited test conditions(1)(2)

Symbol	Parameter	Test conditions	Typ	Max(3)	Unit
ET	Total unadjusted error	f_{PCLK2} = 28 MHz, f_{ADC} = 14 MHz, R_{AIN} < 10 kΩ, V_{DDA} = 3 V to 3.6 V, T_A = 25 °C Measurements made after ADC calibration V_{REF+} = V_{DDA}	±1.3	±2	LSB
EO	Offset error		±1	±1.5	
EG	Gain error		±0.5	±1.5	
ED	Differential linearity error		±0.7	±1	
EL	Integral linearity error		±0.8	±1.5	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
   Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 5.3.13* does not affect the ADC accuracy.
3. Guaranteed by characterization results.

Figure 50. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are available only on 100-pin packages.

5.3.19 DAC electrical specifications

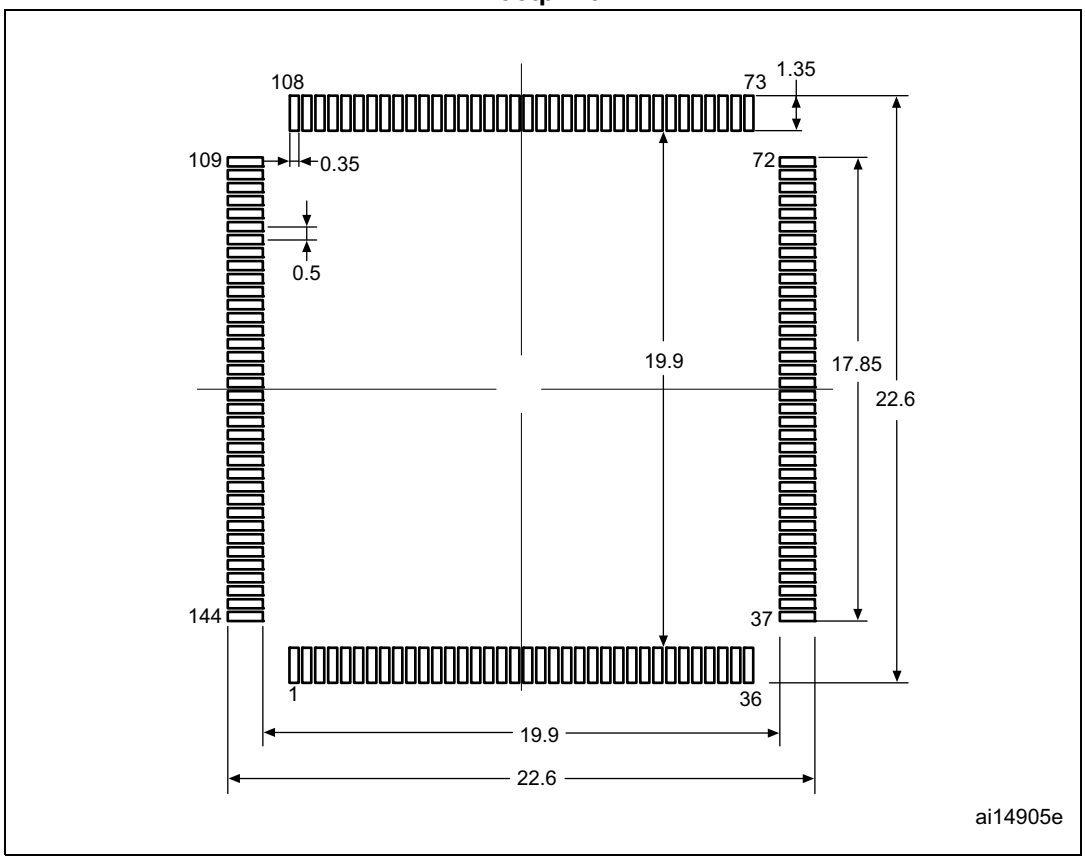
Table 60. DAC characteristics

Symbol	Parameter	Conditions		Min	Typ	Max(1)	Unit	Comments
V_{DDA}	Analog supply voltage			2.4	-	3.6	V	-
V_{REF+}	Reference supply voltage			2.4	-	3.6	V	V_{REF+} must always be below V_{DDA}
V_{SSA}	Ground			0	-	0	V	-
R_{LOAD}(2)	Resistive load with buffer ON	DAC output buffer ON	R_{LOAD} connected to V_{SSA}	5	-	-	kΩ	-
			R_{LOAD} connected to V_{DDA}	25	-	-		-
R_O(2)	Impedance output with buffer OFF			-	-	15	kΩ	When the buffer is OFF, the minimum resistive load between DAC_OUT and V_{SS} to have a 1% accuracy is 1.5 MΩ
C_{LOAD}(2)	Capacitive load			-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).

Table 60. DAC characteristics (continued)

Symbol	Parameter	Conditions		Min	Typ	Max(1)	Unit	Comments
$DAC\_OUT\ min^{(2)}$	Lower DAC_OUT voltage with buffer ON			0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{REF+} = 3.6 V and (0x155) and (0xEAB) at V_{REF+} = 2.4 V.
$DAC\_OUT\ max^{(2)}$	Higher DAC_OUT voltage with buffer ON			-	-	V_{DDA} – 0.2	V	
$DAC\_OUT\ min^{(2)}$	Lower DAC_OUT voltage with buffer OFF			-	0.5	-	mV	It gives the maximum output excursion of the DAC.
$DAC\_OUT\ max^{(2)}$	Higher DAC_OUT voltage with buffer OFF			-	-	V_{REF+} – 1LSB	V	
$I_{DDVREF+}$	DAC DC current consumption in quiescent mode (Standby mode)			-	-	220	µA	With no load, worst code (0xF1C) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs.
I_{DDA}	DAC DC current consumption in quiescent mode(3)			-	-	380	µA	With no load, middle code (0x800) on the inputs.
				-	-	480	µA	With no load, worst code (0xF1C) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs.
DNL(1)	Differential non linearity Difference between two consecutive code-1LSB)			-	-	±0.5	LSB	Given for the DAC in 10-bit configuration.
				-	-	±2	LSB	Given for the DAC in 12-bit configuration.
INL(1)	Integral non linearity (difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)			-	-	±1	LSB	Given for the DAC in 10-bit configuration.
				-	-	±4	LSB	Given for the DAC in 12-bit configuration.
Offset(1)	Offset error (difference between measured value at Code (0x800) and the ideal value = V_{REF+}/2)			-	-	±10	mV	-
				-	-	±3	LSB	Given for the DAC in 10-bit at V_{REF+} = 3.6 V.
				-	-	±12	LSB	Given for the DAC in 12-bit at V_{REF+} = 3.6 V.
Gain error(1)	Gain error			-	-	±0.5	%	Given for the DAC in 12bit configuration.

Figure 53. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package footprint



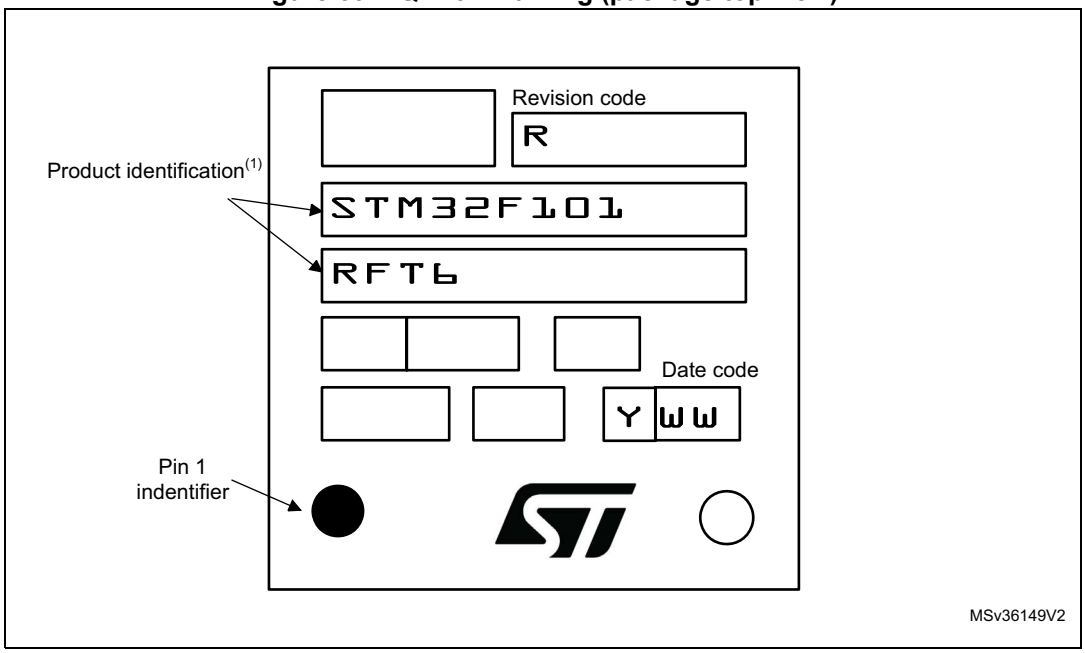
1. Dimensions are expressed in millimeters.

Device marking for LQFP64

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 60. LQFP64 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.